

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1943	((438/424) or (438/427) or (438/426)).CCLS.	US-PGPUB ; USPAT; USOCR	OR	OFF	2005/11/16 16:27
L2	1065	1 (photoresist or photosensitive)	US-PGPUB ; USPAT; EPO; JPO	AND	OFF	2005/11/16 16:27
L3	964	2 mask	US-PGPUB ; USPAT; EPO; JPO	AND	OFF	2005/11/16 16:27
L4	445	3 (implant or implantation)	US-PGPUB ; USPAT; EPO; JPO	AND	OFF	2005/11/16 16:28

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	second adj photoresist near4 first adj photoresist	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 14:59
L2	0	second adj photoresist near6 first adj photoresist	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 15:00
L3	3686	second adj photoresist same first adj photoresist	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 15:00
L4	56168	second adj opening	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 15:00
L5	279	3 and 4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 15:01
L6	217839	sti or stack adj trench or stacked adj trench	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 15:02
L7	15	5 and 6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 15:11
L8	752	oxygen adj implantation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 15:12

L9	80	6 and 8	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/11/16 15:12
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Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	64506	trench	US-PGPUB ; USPAT; EPO; JPO	AND	OFF	2005/11/16 07:55
L2	6459	pad adj oxide	US-PGPUB ; USPAT; EPO; JPO	AND	OFF	2005/11/16 07:55
L3	115717	silicon adj nitride	US-PGPUB ; USPAT; EPO; JPO	AND	OFF	2005/11/16 07:55
L4	2050	(implant or implanting) same oxygen same ions	US-PGPUB ; USPAT; EPO; JPO	AND	OFF	2005/11/16 07:56
L5	925671	oxide	US-PGPUB ; USPAT; EPO; JPO	AND	OFF	2005/11/16 07:56
L6	11655	thermal adj diffusion	US-PGPUB ; USPAT; EPO; JPO	AND	OFF	2005/11/16 07:56
L7	370512	etch or etching	US-PGPUB ; USPAT; EPO; JPO	AND	OFF	2005/11/16 07:56
L8	3	1 2 3 4 5 6 7	US-PGPUB ; USPAT; EPO; JPO	AND	OFF	2005/11/16 07:58
L9	22	1 3 4 5 6 7	US-PGPUB ; USPAT; EPO; JPO	AND	OFF	2005/11/16 08:13
L10	8498	forming adj trench	US-PGPUB ; USPAT; EPO; JPO	AND	OFF	2005/11/16 08:10
L11	7001	5 10	US-PGPUB ; USPAT; EPO; JPO	AND	OFF	2005/11/16 08:10
L12	93	11 4	US-PGPUB ; USPAT; EPO; JPO	AND	OFF	2005/11/16 08:11
L13	65	12 3	US-PGPUB ; USPAT; EPO; JPO	AND	OFF	2005/11/16 08:11

L14	8	13 6	US-PGPUB ; USPAT; EPO; JPO	AND	OFF	2005/11/16 08:11
L15	6459	pad adj oxide	US-PGPUB ; USPAT; EPO; JPO	AND	OFF	2005/11/16 08:13
L16	115717	silicon adj nitride	US-PGPUB ; USPAT; EPO; JPO	AND	OFF	2005/11/16 08:13
L17	4574	15 16	US-PGPUB ; USPAT; EPO; JPO	AND	OFF	2005/11/16 08:14
L18	1315986	substrate	US-PGPUB ; USPAT; EPO; JPO	AND	OFF	2005/11/16 08:14
L19	4509	17 18	US-PGPUB ; USPAT; EPO; JPO	AND	OFF	2005/11/16 08:14
L20	3071	19 (etch or etching) trench	US-PGPUB ; USPAT; EPO; JPO	AND	OFF	2005/11/16 08:14
L21	1408	(implant or implanting) adj oxygen	US-PGPUB ; USPAT; EPO; JPO	AND	OFF	2005/11/16 08:15
L22	57	20 21	US-PGPUB ; USPAT; EPO; JPO	AND	OFF	2005/11/16 08:15
L23	11655	thermal adj diffusion	US-PGPUB ; USPAT; EPO; JPO	AND	OFF	2005/11/16 08:15
L24	3	22 23	US-PGPUB ; USPAT; EPO; JPO	AND	OFF	2005/11/16 08:15